

## Trench gate field-stop IGBT, M series 650 V, 10 A low loss

Datasheet - production data

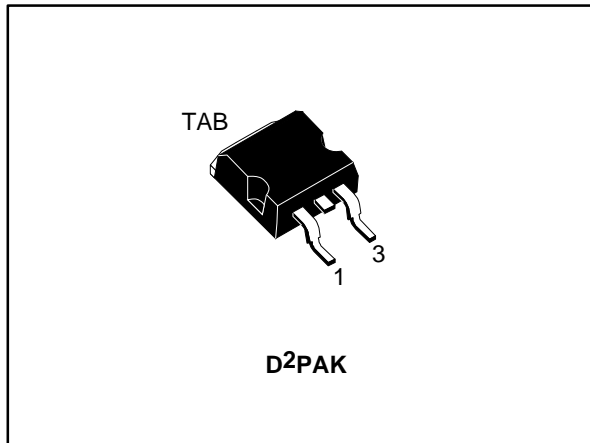
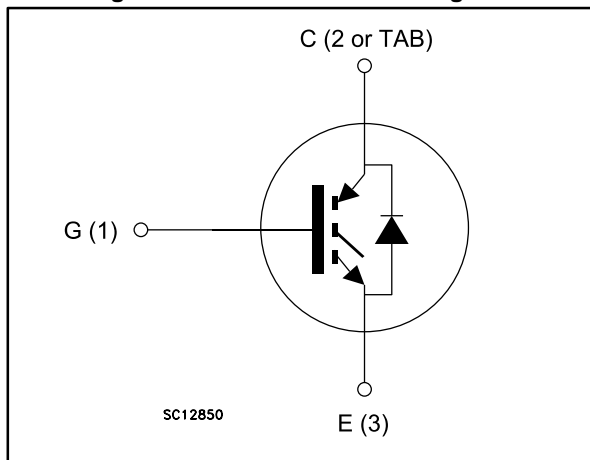


Figure 1: Internal schematic diagram



### Features

- 6  $\mu$ s of short-circuit withstand time
- $V_{CE(sat)} = 1.55$  V (typ.) @  $I_C = 10$  A
- Tight parameter distribution
- Safer paralleling
- Low thermal resistance
- Soft and very fast recovery antiparallel diode

### Applications

- Motor control
- UPS
- PFC

### Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the M series of IGBTs, which represents an optimum compromise in performance to maximize the efficiency of inverter systems where low loss and short-circuit capability are essential. Furthermore, a positive  $V_{CE(sat)}$  temperature coefficient and tight parameter distribution result in safer paralleling operation.

Table 1: Device summary

Order code	Marking	Package	Packing
STGB10M65DF2	G10M65DF2	D <sup>2</sup> PAK	Tape and reel

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage ( $V_{GE} = 0$ )	650	V
$I_C$	Continuous collector current at $T_C = 25\text{ °C}$	20	A
	Continuous collector current at $T_C = 100\text{ °C}$	10	
$I_{CP}^{(1)}$	Pulsed collector current	40	A
$V_{GE}$	Gate-emitter voltage	$\pm 20$	V
$I_F$	Continuous forward current at $T_C = 25\text{ °C}$	20	A
	Continuous forward current at $T_C = 100\text{ °C}$	10	
$I_{FP}^{(1)}$	Pulsed forward current	40	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	115	W
$T_{STG}$	Storage temperature range	- 55 to 150	°C
$T_J$	Operating junction temperature	- 55 to 175	

**Notes:**

<sup>(1)</sup>Pulse width limited by maximum junction temperature.

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance junction-case IGBT	1.3	°C/W
$R_{thJC}$	Thermal resistance junction-case diode	2.08	
$R_{thJA}$	Thermal resistance junction-ambient	62.5	

## 2 Electrical characteristics

$T_C = 25\text{ °C}$  unless otherwise specified

**Table 4: Static characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$ , $I_C = 2\text{ mA}$	650			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$ , $I_C = 10\text{ A}$		1.55	2.0	V
		$V_{GE} = 15\text{ V}$ , $I_C = 10\text{ A}$ , $T_J = 125\text{ °C}$		1.9		
		$V_{GE} = 15\text{ V}$ , $I_C = 10\text{ A}$ , $T_J = 175\text{ °C}$		2.1		
$V_F$	Forward on-voltage	$I_F = 10\text{ A}$		1.5		V
		$I_F = 10\text{ A}$ , $T_J = 125\text{ °C}$		1.3		
		$I_F = 10\text{ A}$ , $T_J = 175\text{ °C}$		1.2		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$ , $I_C = 250\text{ }\mu\text{A}$	5	6	7	V
$I_{CES}$	Collector cut-off current	$V_{GE} = 0\text{ V}$ , $V_{CE} = 650\text{ V}$			25	$\mu\text{A}$
$I_{GES}$	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$ , $V_{GE} = \pm 20\text{ V}$			250	$\mu\text{A}$

**Table 5: Dynamic characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance	$V_{CE} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GE} = 0\text{ V}$	-	840	-	pF
$C_{oes}$	Output capacitance		-	63	-	
$C_{res}$	Reverse transfer capacitance		-	16	-	
$Q_g$	Total gate charge	$V_{CC} = 520\text{ V}$ , $I_C = 10\text{ A}$ , $V_{GE} = 15\text{ V}$ (see <a href="#">Figure 30: "Gate charge test circuit"</a> )	-	28	-	nC
$Q_{ge}$	Gate-emitter charge		-	6	-	
$Q_{gc}$	Gate-collector charge		-	12	-	

**Table 6: IGBT switching characteristics (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$ , $I_C = 10\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 22\text{ }\Omega$ (see <a href="#">Figure 29: "Test circuit for inductive load switching"</a> )	-	19	-	ns
$t_r$	Current rise time		-	7.4	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1086	-	A/ $\mu\text{s}$
$t_{d(off)}$	Turn-off-delay time		-	91	-	ns

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
$t_f$	Current fall time		-	92	-	ns	
$E_{on(1)}$	Turn-on switching losses		-	0.12	-	mJ	
$E_{off(2)}$	Turn-off switching losses		-	0.27	-	mJ	
$E_{ts}$	Total switching losses		-	0.39	-	mJ	
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$ , $I_C = 10\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 22\ \Omega$ $T_J = 175\text{ }^\circ\text{C}$ (see <a href="#">Figure 29: "Test circuit for inductive load switching"</a> )	-	18	-	ns	
$t_r$	Current rise time		-	9	-	ns	
$(di/dt)_{on}$	Turn-on current slope		-	890	-	A/ $\mu\text{s}$	
$t_{d(off)}$	Turn-off-delay time		-	90	-	ns	
$t_f$	Current fall time		-	170	-	ns	
$E_{on}$	Turn-on switching losses		-	0.26	-	mJ	
$E_{off}$	Turn-off switching losses		-	0.4	-	mJ	
$E_{ts}$	Total switching losses		-	0.66	-	mJ	
$t_{sc}$	Short-circuit withstand time		$V_{CC} \leq 400\text{ V}$ , $V_{GE} = 15\text{ V}$ , $T_{Jstart} = 150\text{ }^\circ\text{C}$	6		-	$\mu\text{s}$

**Notes:**

(1)Energy losses include reverse recovery of the diode.

(2)Turn-off losses also include the tail of the collector current.

**Table 7: Diode switching characteristics (inductive load)**

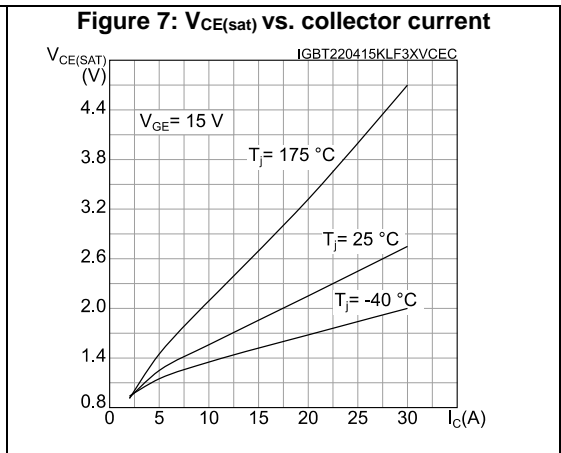
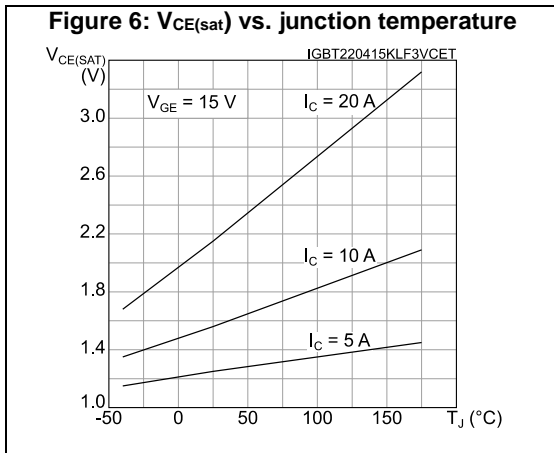
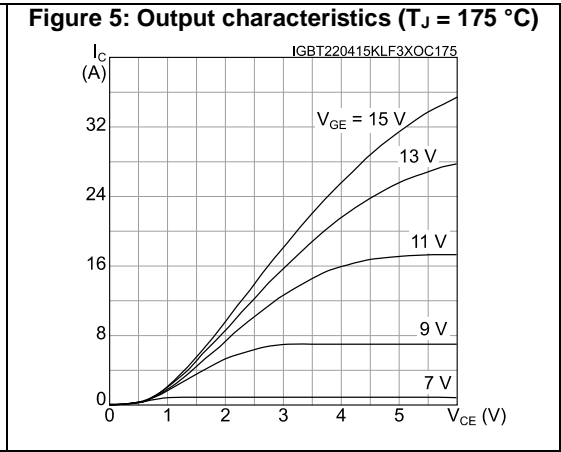
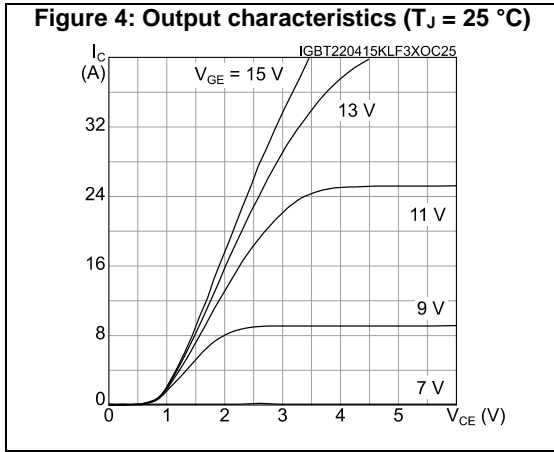
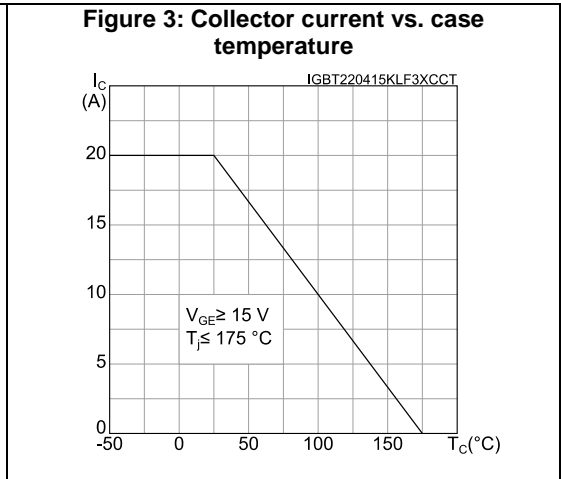
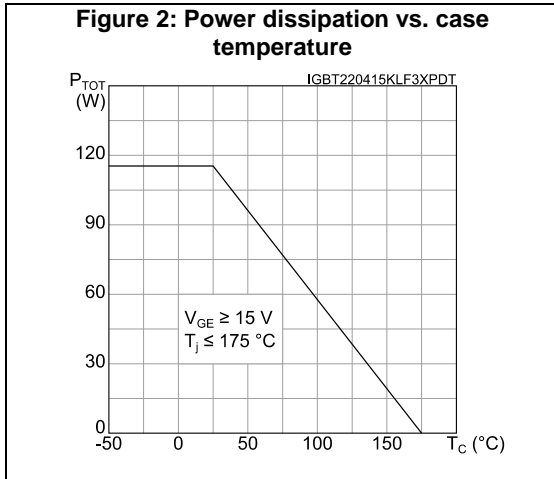
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{rr}$	Reverse recovery time	$I_F = 10\text{ A}$ , $V_R = 400\text{ V}$ , $V_{GE} = 15\text{ V}$ (see <a href="#">Figure 29: "Test circuit for inductive load switching"</a> ) $di/dt = 1000\text{ A}/\mu\text{s}$	-	96		ns
$Q_{rr}$	Reverse recovery charge		-	373		nC
$I_{rrm}$	Reverse recovery current		-	13		A
$dl_{rr}/dt$	Peak rate of fall of reverse recovery current during $t_b$		-	661		A/ $\mu\text{s}$

Electrical characteristics

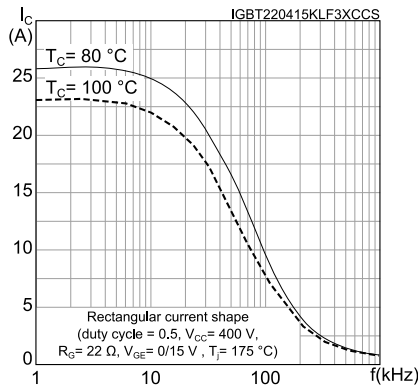
STGB10M65DF2

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{rr}$	Reverse recovery energy	$I_F = 10\text{ A}$ , $V_R = 400\text{ V}$ , $V_{GE} = 15\text{ V}$ $T_J = 175\text{ °C}$ (see <a href="#">Figure 29: "Test circuit for inductive load switching"</a> ) $di/dt = 1000\text{ A/}\mu\text{s}$	-	52		$\mu\text{J}$
$t_{rr}$	Reverse recovery time		-	201		ns
$Q_{rr}$	Reverse recovery charge		-	1352		nC
$I_{rrm}$	Reverse recovery current		-	19		A
$di_{rr}/dt$	Peak rate of fall of reverse recovery current during $t_b$		-	405		A/ $\mu\text{s}$
$E_{rr}$	Reverse recovery energy		-	150		$\mu\text{J}$

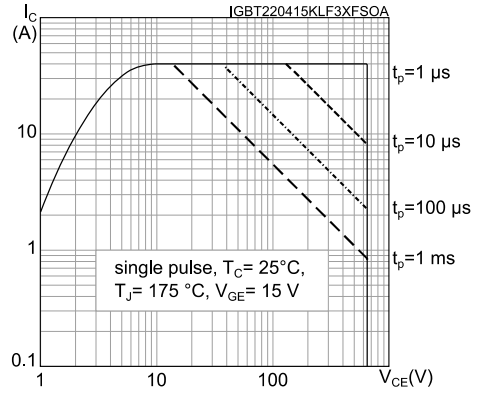
2.1 Electrical characteristics (curves)



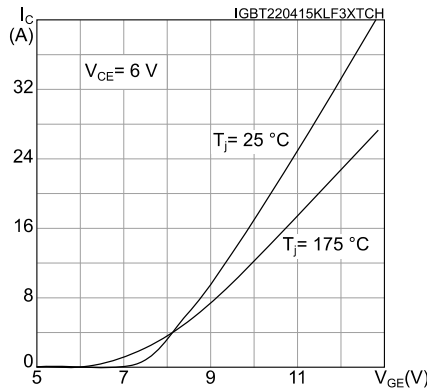
**Figure 8: Collector current vs. switching frequency**



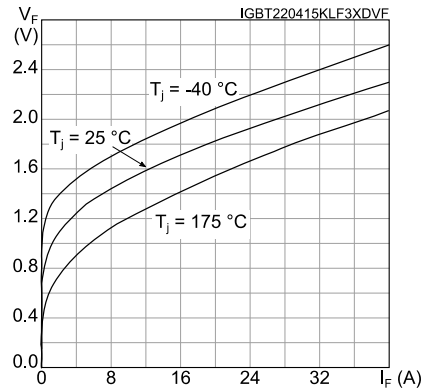
**Figure 9: Forward bias safe operating area**



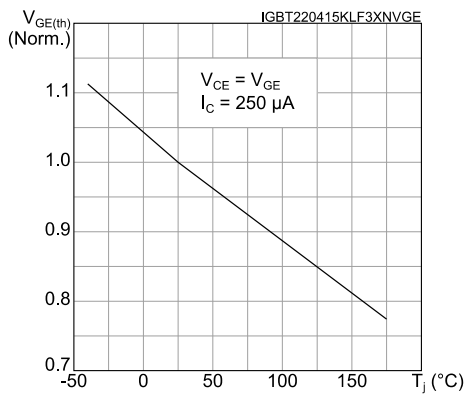
**Figure 10: Transfer characteristics**



**Figure 11: Diode V\_F vs. forward current**



**Figure 12: Normalized V\_GE(th) vs. junction temperature**



**Figure 13: Normalized V\_(BR)CES vs. junction temperature**

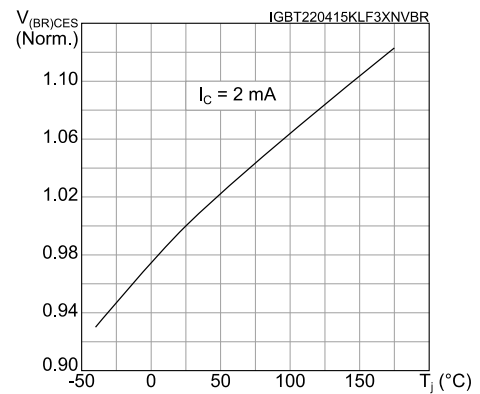




Figure 14: Capacitance variations

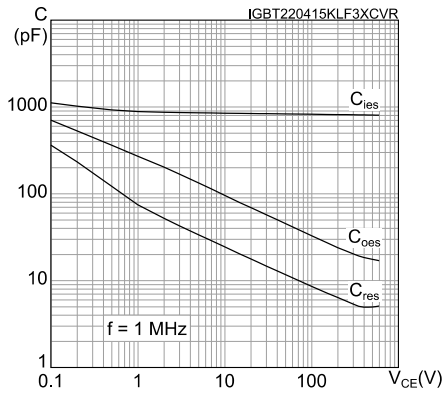


Figure 15: Gate charge vs. gate-emitter voltage

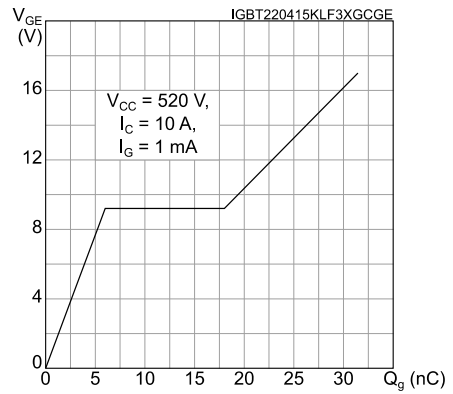


Figure 16: Switching loss vs. collector current

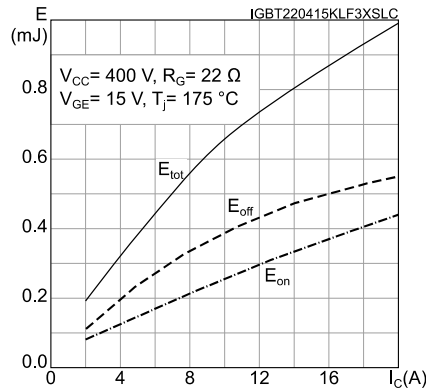


Figure 17: Switching loss vs. gate resistance

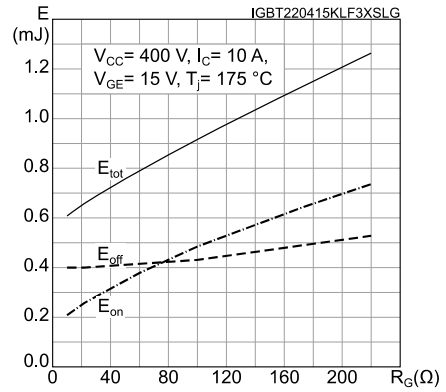


Figure 18: Switching loss vs. temperature

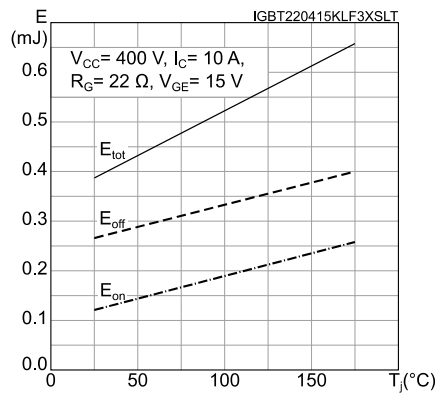


Figure 19: Switching loss vs. collector emitter voltage

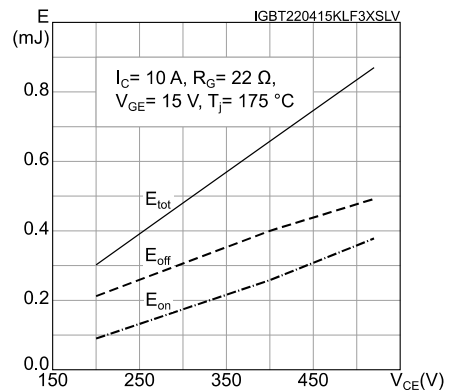


Figure 20: Short-circuit time and current vs.  $V_{GE}$

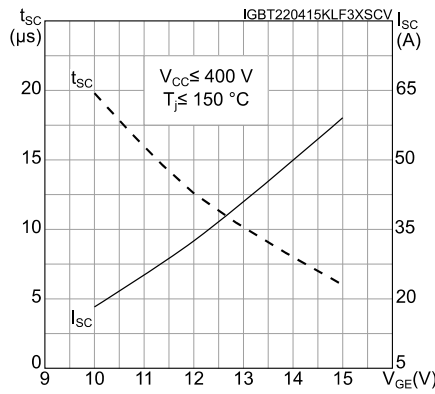


Figure 21: Switching times vs. collector current

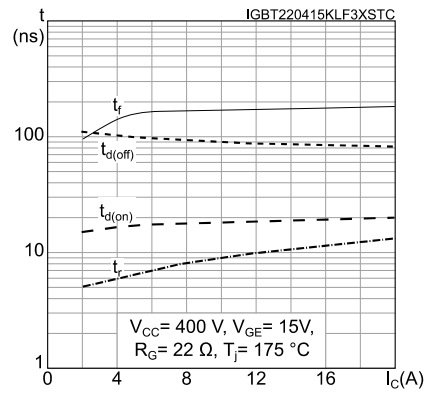


Figure 22: Switching times vs. gate resistance

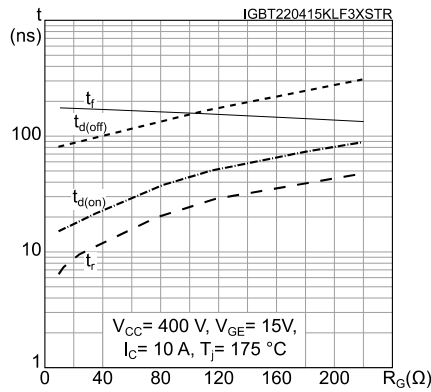


Figure 23: Reverse recovery current vs. diode current slope

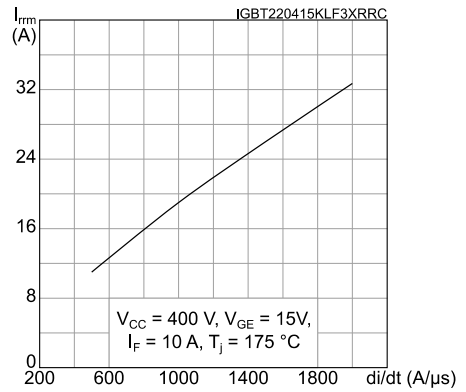


Figure 24: Reverse recovery time vs. diode current slope

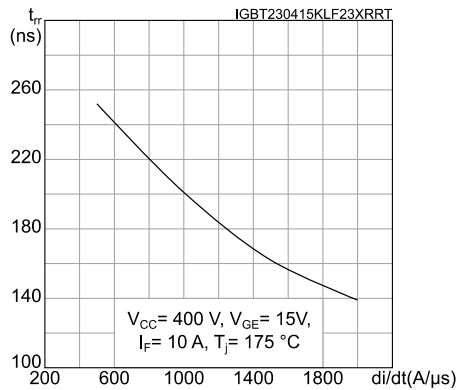


Figure 25: Reverse recovery charge vs. diode current slope

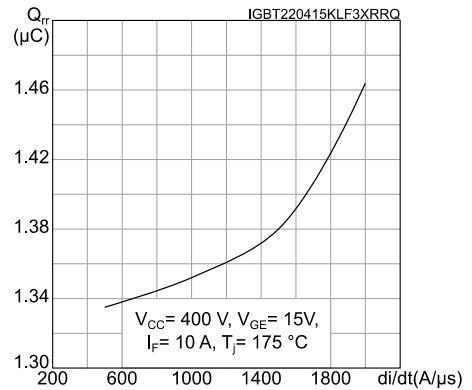


Figure 26: Reverse recovery energy vs. diode current slope

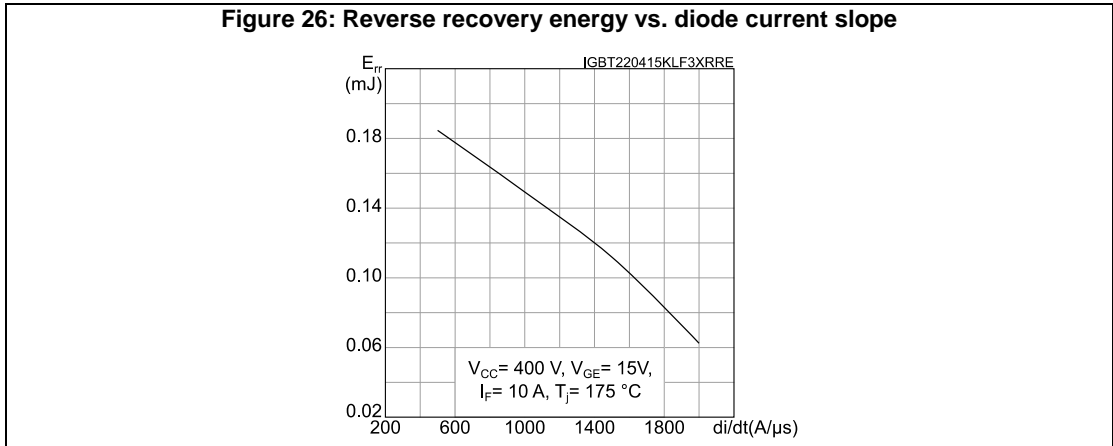


Figure 27: Thermal impedance for IGBT

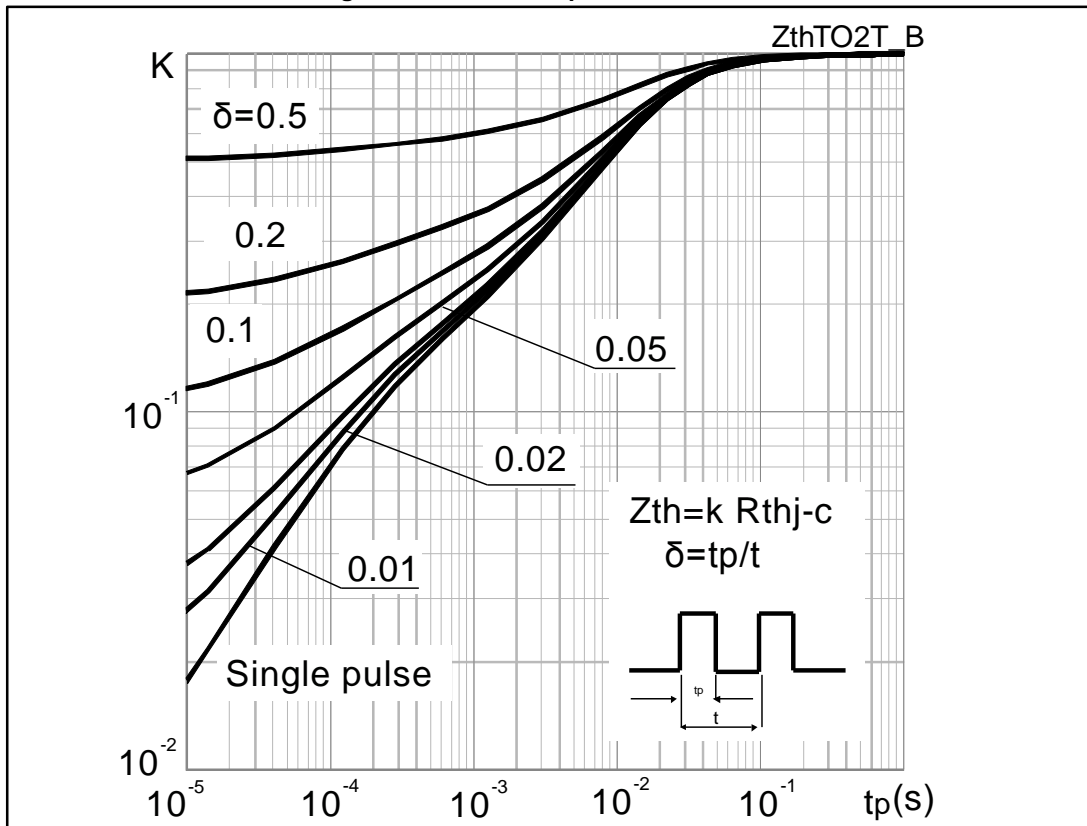
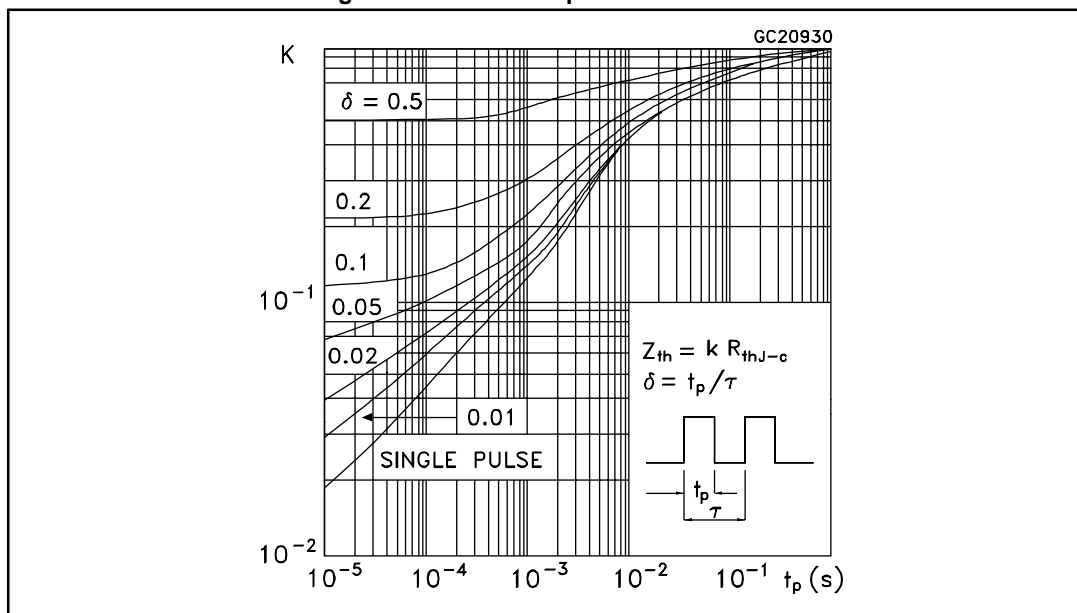


Figure 28: Thermal impedance for diode





## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 D<sup>2</sup>PAK package information

Figure 33: D<sup>2</sup>PAK (TO-263) type A package outline

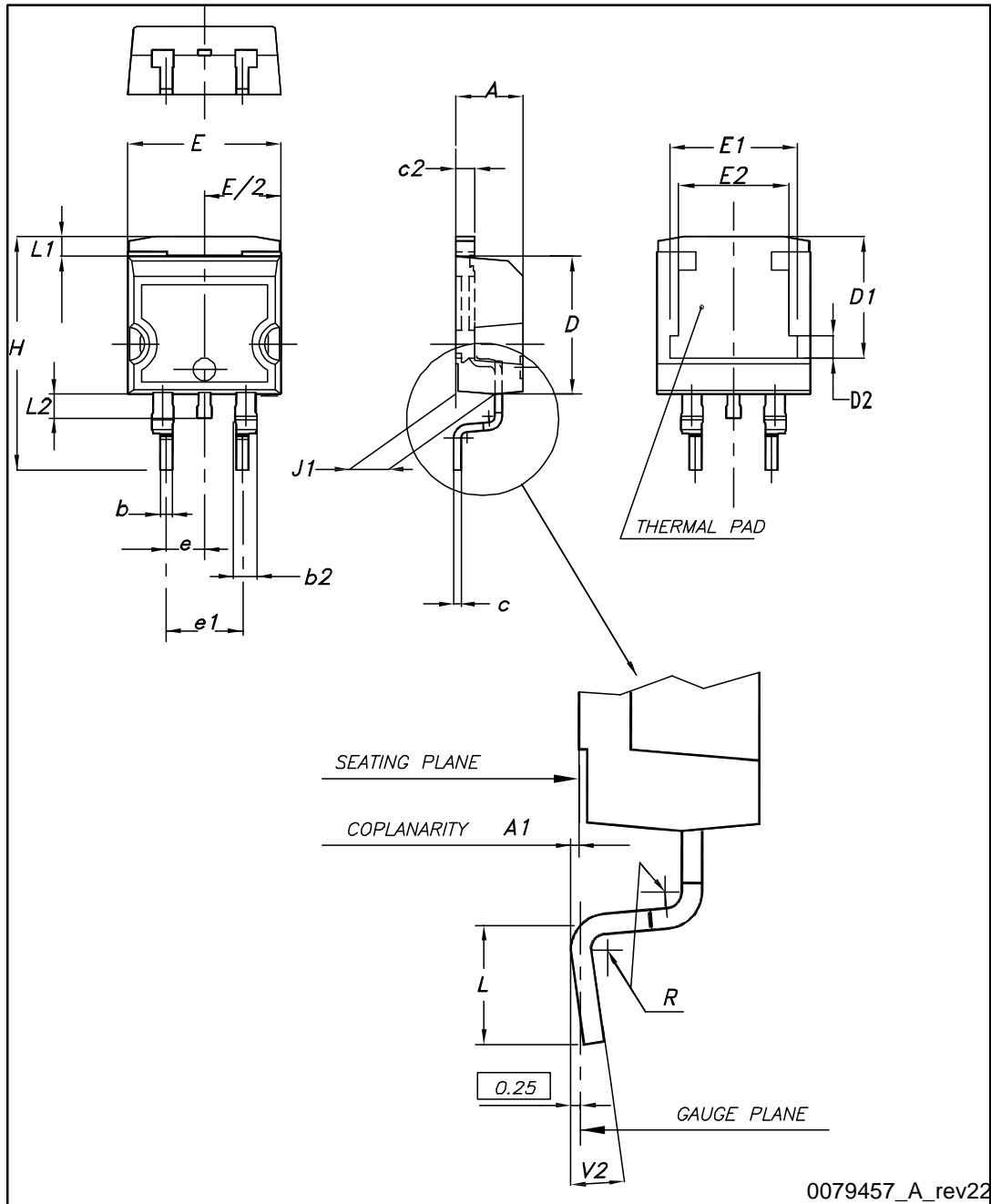
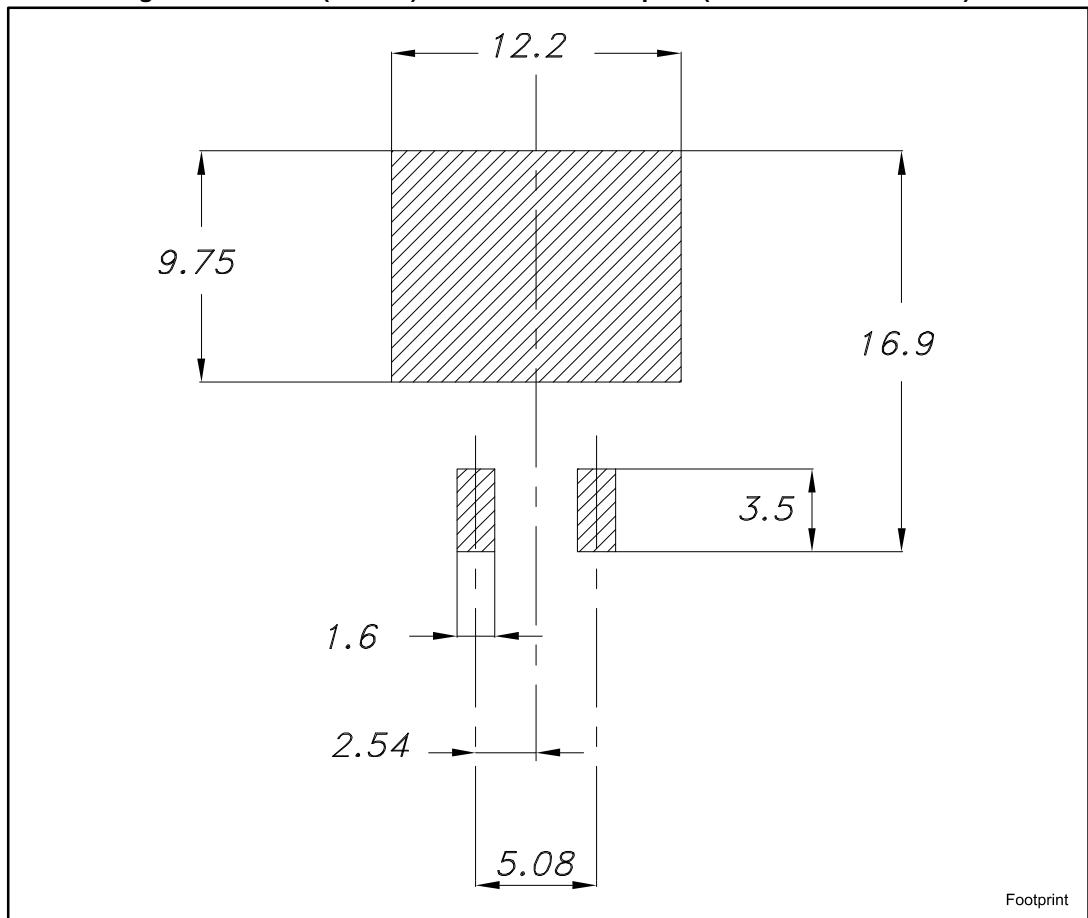


Table 8: D<sup>2</sup>PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10		10.40
E1	8.50	8.70	8.90
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 34: D<sup>2</sup>PAK (TO-263) recommended footprint (dimensions are in mm)





### 4.2 D<sup>2</sup>PAK packing information

Figure 35: Tape outline

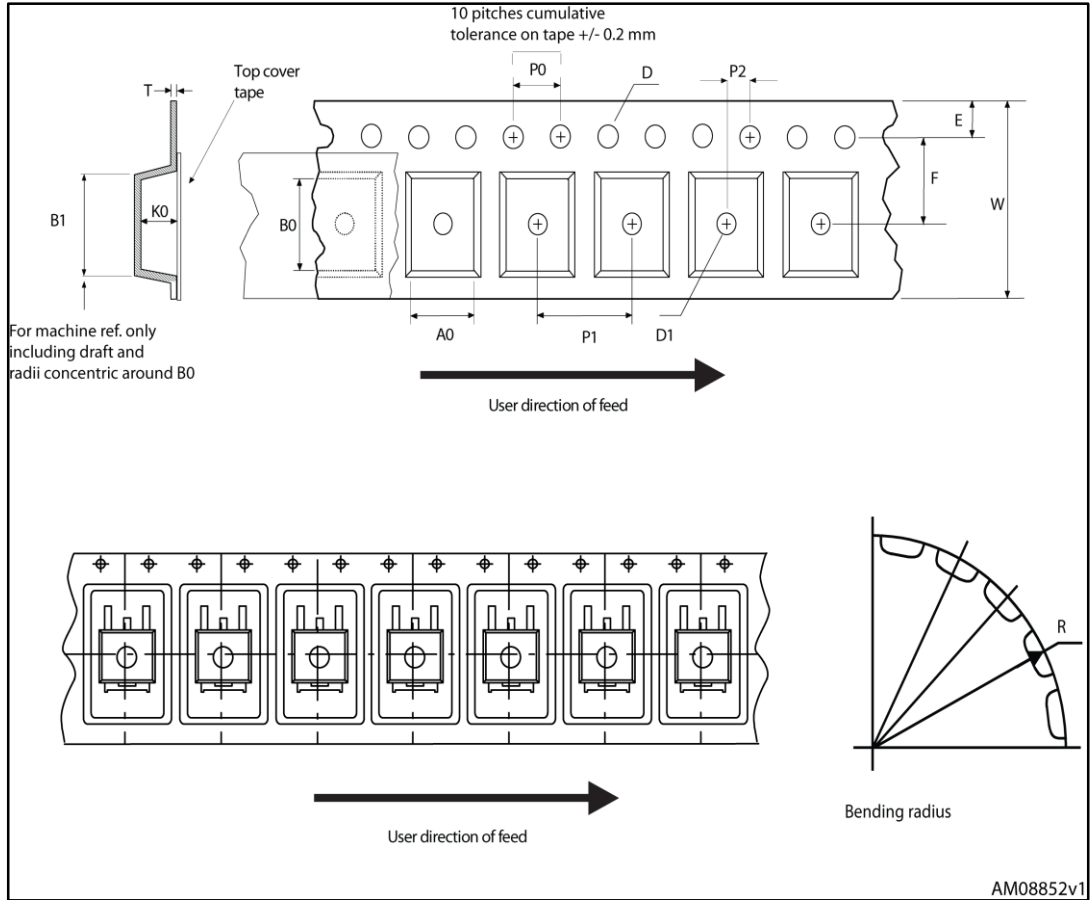
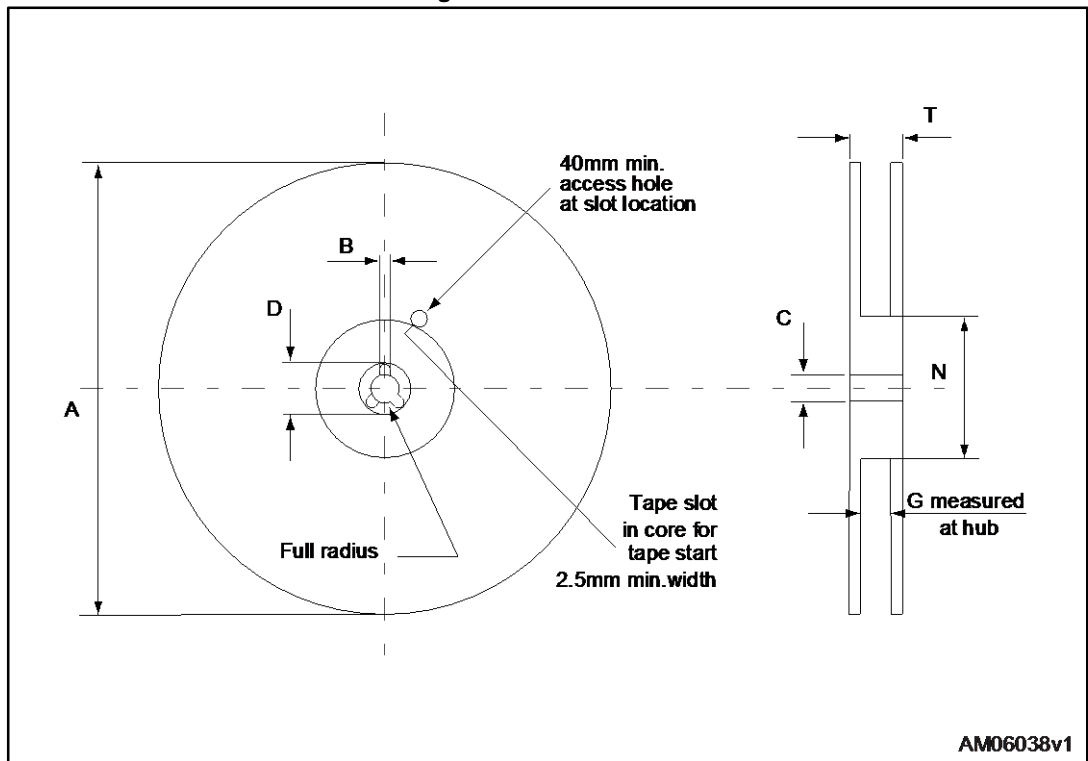


Figure 36: Reel outline



AM06038v1

Table 9: D<sup>2</sup>PAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

## 5 Revision history

**Table 10: Document revision history**

Date	Revision	Changes
10-Feb-2015	1	First release.
23-Apr-2015	2	Minor text edits throughout document In Section 2 Electrical characteristics: - updated Table 4: Static characteristics - updated Table 5: Dynamic characteristics - updated Table 6: IGBT switching characteristics (inductive load) - updated Table 7: Diode switching characteristics (inductive load) Added Section 2.1 Electrical characteristics (curves)
11-Jun-2015	3	Document status promoted from preliminary to production data.
31-Jul-2015	4	Updated table titled: "Diode switching characteristics (inductive load)".
20-Oct-2015	5	Updated <a href="#">Table 5: "Dynamic characteristics"</a> and <a href="#">Table 6: "IGBT switching characteristics (inductive load)"</a> . Updated <a href="#">Figure 8: "Collector current vs. switching frequency"</a> .

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